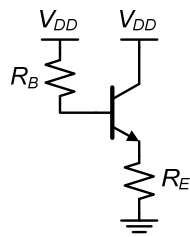


NPN Large Signal (Assume FAR)

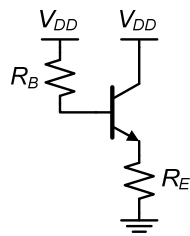


$V_{DD} = 10V$
 $\beta = 100$
 $V_A = \text{infinity}$
 $R_B = 1k$
 $R_E = 1k$
 $V_{BEon} = 0.7V$
 $V_{CEsat} = 0.5V$

Solve for I_C

1. Substitute large-signal FAR model
2. Solve for I_C
3. Check assumption

NPN Large Signal (Assume SAT)

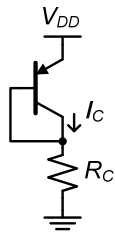


$V_{DD} = 10V$
 $\beta = 100$
 $V_A = \text{infinity}$
 $R_B = 1k$
 $R_E = 1k$
 $V_{BEon} = 0.7V$
 $V_{CEsat} = 0.5V$

Solve for I_C

1. Substitute large-signal SAT model
2. Solve for I_C
3. Check assumption

PNP Large Signal (1)



$V_{DD} = 10V$
 $\beta = 100$
 $V_A = \text{infinity}$
 $R_C = 1k$
 $V_{BEon} = -0.7V$
 $V_{CEsat} = -0.5V$

Solve for I_C

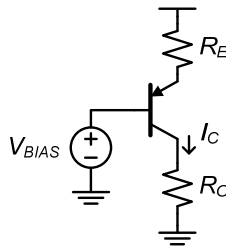
1. Choose region of operation
2. Substitute model
3. Solve for I_C
4. Check assumption

EECS 311 Fall 2008

10/31/2008 Discussion Session

3

PNP Large Signal (2)



Find expression for I_C

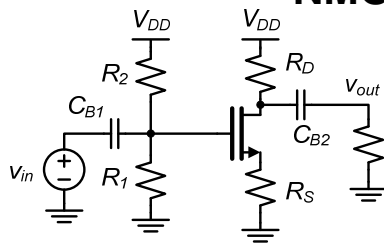
1. Choose region of operation
2. Substitute model
3. Find expression for I_C

EECS 311 Fall 2008

10/31/2008 Discussion Session

4

NMOS DC Model



Find expression for I_D

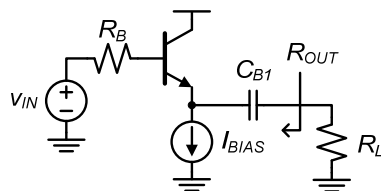
1. Choose region of operation
2. Substitute model
3. Find expression for I_D

EECS 311 Fall 2008

10/31/2008 Discussion Session

5

NPN Small Signal Rout



Neglect r_o in BJT model

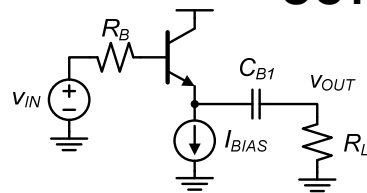
1. Find small signal AC model
2. Apply test source to measure R_{out}
3. $R_{out} = v_t/i_t$

EECS 311 Fall 2008

10/31/2008 Discussion Session

6

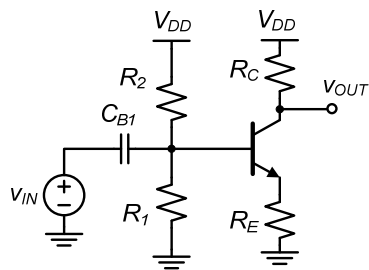
OCTC to Find f_L



Neglect r_o in BJT model

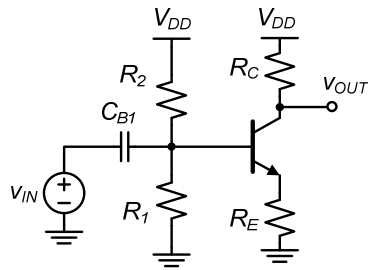
1. Find small signal low-freq model
2. Apply OCTC

NPN Design Example (1)



Find relationship between Power,
DC bias stability, and gain

NPN Design Example (2)



EECS 311 Fall 2008

10/31/2008 Discussion Session

9

EECS 311 Fall 2008

10/31/2008 Discussion Session

10